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		BY APPLICANT		First Named Inventor	Yuanning Chen, et al.				
	O T T T T T T T T T T T T T T T T T T T			Group Art Unit	2813				
	(use as many s	neets as necessary)		Examiner Name	Jack S J Chen				
Sheet	1	of	1	Attorney Docket No.	TI-35022,2				

				U.S. I	PATENT DOCUM	ENTS
		U.S. Patent Document		Name of Patentee	Date of Pub.	
Exam. Initials*	Cite No. ¹	Number	Kind Code ² (if known)	or Applicant of Cited Doc.	of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS					
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	CA	RYUTA TSUCHIYA ET AL., "Femto-Second CMOS Technology with High-k Offset Spacer and SiN Gate Dielectric with Oxygen-Enriched Inteface" IEEE 2002 Symposium on VLSI Technology Digest of Technical Papers				
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